30-PQ12B2A200H703-PK89L07T

datasheet

***flow*BOOST 2 dual** **1200 V / 200 A**

Topology features

- Auxiliary diodes for FC pre-charge (patent pending)
- Dual Flying Cap Booster
- Kelvin Emitter for improved switching performance
- Temperature sensor

Component features

- High speed switching
- Low collector emitter saturation voltage
- Low turn-off losses
- Optimized for hard switching topologies
- Positive temperature coefficient

Housing features

- Base isolation: Al_2O_3
- Convex shaped baseplate for superior thermal contact
- Cu baseplate
- Thermo-mechanical push-and-pull force relief
- Press-fit pin
- Reliable cold welding connection

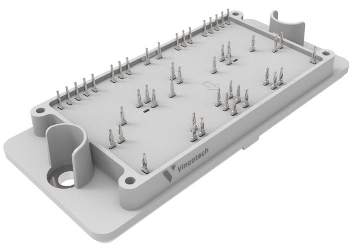
Target applications

- Solar Inverters

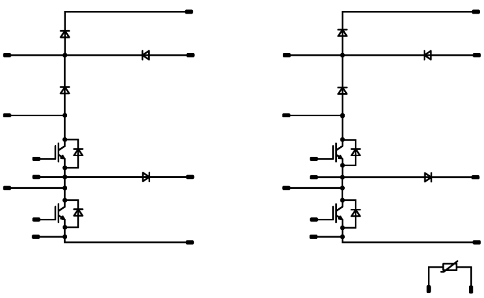
Types

- 30-PQ12B2A200H703-PK89L07T

flow 2 12 mm housing



Schematic



Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions		Value	Unit
Inner Boost Switch					
Collector-emitter voltage	V_{CES}			1200	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$	T_s = 80 °C	156	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}		600	A
Turn off safe operating area		T_j = 150°C, V_{CE} = 1200 V		600	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	287	W
Gate-emitter voltage	V_{GES}			±20	V
Maximum junction temperature	T_{jmax}			175	°C
Inner Boost Diode					
Peak repetitive reverse voltage	V_{RRM}			1200	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	132	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		255	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 10 ms	T_j = 110 °C	645	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	268	W
Maximum junction temperature	T_{jmax}			175	°C
Inner Boost Sw. Protection Diode					
Peak repetitive reverse voltage	V_{RRM}			1600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	78	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 10 ms	T_j = 150 °C	480	A
Surge current capability	I^2t			1100	A^2s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	92	W
Maximum junction temperature	T_{jmax}			150	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions		Value	Unit
Outer Boost Switch					
Collector-emitter voltage	V_{CES}			1200	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$	T_s = 80 °C	156	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}		600	A
Turn off safe operating area		T_j = 150°C, V_{CE} = 1200 V		600	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	287	W
Gate-emitter voltage	V_{GES}			±20	V
Maximum junction temperature	T_{jmax}			175	°C
Outer Boost Diode					
Peak repetitive reverse voltage	V_{RRM}			1200	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	132	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		255	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 10 ms	T_j = 110 °C	645	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	268	W
Maximum junction temperature	T_{jmax}			175	°C
Outer Boost Sw. Protection Diode					
Peak repetitive reverse voltage	V_{RRM}			1600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	78	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 10 ms	T_j = 150 °C	480	A
Surge current capability	I^2t			1100	A^2s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	92	W
Maximum junction temperature	T_{jmax}			150	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions		Value	Unit
Aux Diode					
Peak repetitive reverse voltage	V_{RRM}			1200	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	74	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		150	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 10 ms	T_j = 25 °C	600	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	145	W
Maximum junction temperature	T_{jmax}			175	°C
Module Properties					
Thermal Properties					
Storage temperature	T_{stg}			-40…+125	°C
Operation temperature under switching condition	T_{jop}			-40…+(T_{jmax} - 25)	°C
Isolation Properties					
Isolation voltage	V_{isol}	DC Test Voltage*	t_p = 2 s	6800	V
Creepage distance				>12,7	mm
Clearance				>12,7	mm
Comparative Tracking Index	CTI			≥ 600	

*100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Values Min	Values Typ	Values Max	Unit
Inner Boost Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,0032	25	4,7	5,5	6,2	V
Collector-emitter saturation voltage	V_{CEsat}		15		200	25 125 150		1,78 1,94 1,98	2,15[1]	V
Collector-emitter cut-off current	I_{CES}		0	1200		25			8	μA
Gate-emitter leakage current	I_{GES}		20	0		25			200	nA
Internal gate resistance	r_g							None		Ω
Input capacitance	C_{ies}	f = 100 kHz	0	25		25		26000		pF
Output capacitance	C_{oes}							480		pF
Reverse transfer capacitance	C_{res}							144		pF
Gate charge	Q_g	V_{CC} = 960 V	0/15		200	25		1428		nC
Thermal										
Thermal resistance junction to sink[2]	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,33		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 2 Ω R_{goff} = 2 Ω	±15	700	200	25 125 150		157,12 159,93 161,44		ns
Rise time	t_r					25 125 150		11,58 13,33 13,42		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		166,82 199,5 208,02		ns
Fall time	t_f					25 125 150		34,93 51,67 61,02		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=1,09 μC Q_{rFWD}=1,09 μC Q_{rFWD}=1,09 μC				25 125 150		4,8 4,98 5,04		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		5,42 8,51 9,41		mWs

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	Unit
Inner Boost Diode										
Static										
Forward voltage	V_F				100	25 125 150		1,41 1,61 1,71	2(1)	V
Reverse leakage current	I_R	V_r = 1200 V				25		25	2500	µA
Thermal										
Thermal resistance junction to sink(2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,35		K/W
Dynamic										
Peak recovery current	I_{RM}	d*i*/d*t*=10798 A/µs d*i*/d*t*=11553 A/µs d*i*/d*t*=11040 A/µs	±15	700	200	25 125 150		96,61 100,64 101,96		A
Reverse recovery time	t_{rr}					25 125 150		21,14 20,65 20,55		ns
Recovered charge	Q_r					25 125 150		1,09 1,09 1,09		µC
Reverse recovered energy	E_{rec}					25 125 150		0,203 0,21 0,208		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		8397,35 9409,83 9802,5		A/µs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Inner Boost Sw. Protection Diode										
Static										
Forward voltage	V_F				40	25 125 150		1,06 0,987 0,974	1,5[(1)]	V
Reverse leakage current	I_R	V_r = 1600 V				25 150			100 2000	µA
Thermal										
Thermal resistance junction to sink[(2)]	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,76		K/W

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Values Min	Typ	Max	Unit
Outer Boost Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,0032	25	4,7	5,5	6,2	V
Collector-emitter saturation voltage	V_{CEsat}		15		200	25 125 150		1,78 1,94 1,98	2,15(1)	V
Collector-emitter cut-off current	I_{CES}		0	1200		25			8	µA
Gate-emitter leakage current	I_{GES}		20	0		25			200	nA
Internal gate resistance	r_g							None		Ω
Input capacitance	C_{ies}							26000		pF
Output capacitance	C_{oes}	f = 100 kHz	0	25		25		480		pF
Reverse transfer capacitance	C_{res}							144		pF
Gate charge	Q_g	V_{CC} = 960 V	0/15		200	25		1428		nC
Thermal										
Thermal resistance junction to sink(2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,33		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$					25 125 150		153,92 156,67 157,56		ns
Rise time	t_r	R_{gon} = 2 Ω R_{goff} = 2 Ω				25 125 150		13,39 15,35 15,96		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		169,29 202,12 211,22		ns
Fall time	t_f		±15	700	200	25 125 150		31,57 54,67 60,51		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=1,09 µC Q_{rFWD}=1,08 µC Q_{rFWD}=1,08 µC				25 125 150		3,37 3,71 3,77		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		4,79 8,14 9,08		mWs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Outer Boost Diode										
Static										
Forward voltage	V_F				100	25 125 150		1,41 1,61 1,71	2(1)	V
Reverse leakage current	I_R	V_r = 1200 V				25		25	2500	µA
Thermal										
Thermal resistance junction to sink(2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,35		K/W
Dynamic										
Peak recovery current	I_{RM}	d*i*/d*t*=12670 A/µs d*i*/d*t*=13062 A/µs d*i*/d*t*=11703 A/µs	±15	700	200	25 125 150		110,86 109,02 109,29		A
Reverse recovery time	t_{rr}					25 125 150		16,6 17,02 17,18		ns
Recovered charge	Q_r					25 125 150		1,09 1,08 1,08		µC
Reverse recovered energy	E_{rec}					25 125 150		0,164 0,163 0,162		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		26300,44 21954,03 21244,4		A/µs

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	Unit
Outer Boost Sw. Protection Diode										
Static										
Forward voltage	V_F				40	25 125 150		1,06 0,987 0,974	1,5(1)	V
Reverse leakage current	I_R	V_r = 1600 V				25 150			100 2000	µA
Thermal										
Thermal resistance junction to sink(2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,76		K/W
Aux Diode										
Static										
Forward voltage	V_F				75	25 125 150		2,59 2,16 2,07	3,3(1)	V
Reverse leakage current	I_R	V_r = 1200 V				25 150			250 2000	µA
Thermal										
Thermal resistance junction to sink(2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,66		K/W

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Thermistor										
Static										
Rated resistance	R					25		22		kΩ
Deviation of R100	$\Delta_{R/R}$	R_{100} = 1484 Ω				100	-5		5	%
Power dissipation	P					25		130		mW
Power dissipation constant	d					25		1,5		mW/K
B-value	$B_{(25/50)}$	Tol. ±1 %						3962		K
B-value	$B_{(25/100)}$	Tol. ±1 %						4000		K
Vincotech Thermistor Reference									I	

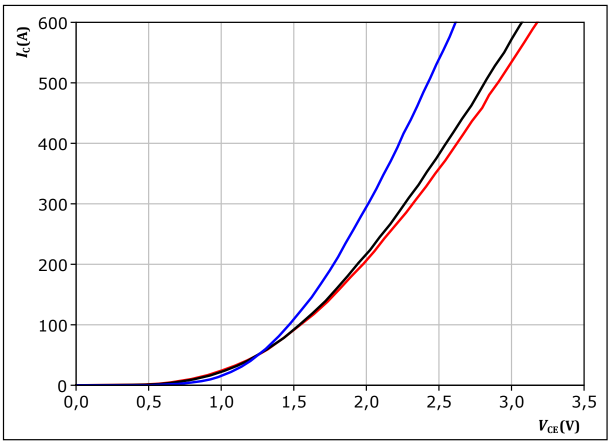
(1) Value at chip level
(2) Only valid with pre-applied Vincotech thermal interface material.

Inner Boost Switch Characteristics

figure 1. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$

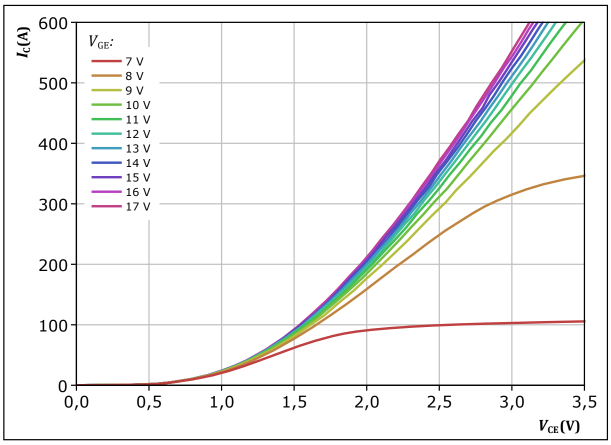


t_p = 250 µs
V_{GE} = 15 V
T_j: 25 °C, 125 °C, 150 °C

figure 2. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$

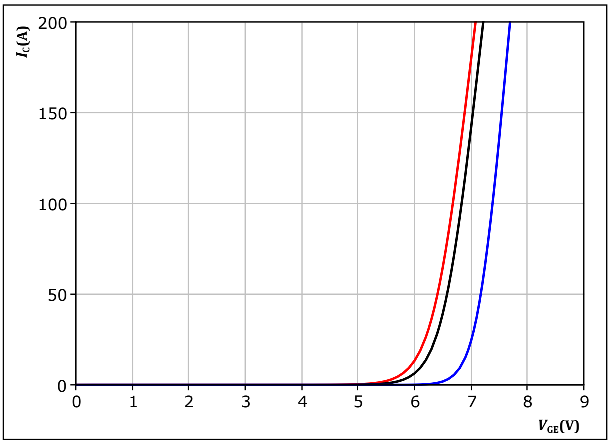


t_p = 250 µs
T_j = 150 °C
V_{GE} from 7 V to 17 V in steps of 1 V

figure 3. **IGBT**

Typical transfer characteristics

$I_C = f(V_{GE})$

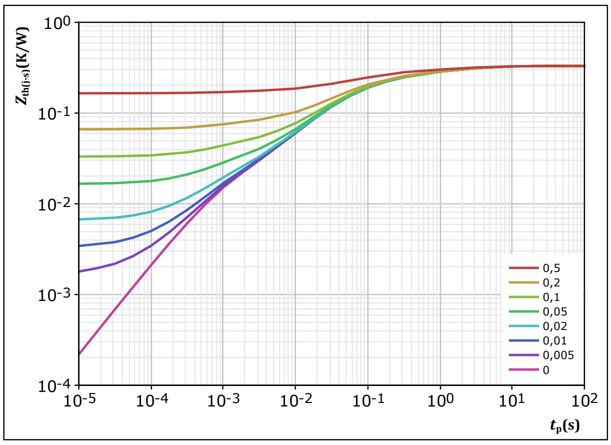


t_p = 250 µs
V_{CE} = 48 V
T_j: 25 °C, 125 °C, 150 °C

figure 4. **IGBT**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D = t_p / T
$R_{th(j-s)}$ = 0,331 K/W

IGBT thermal model values

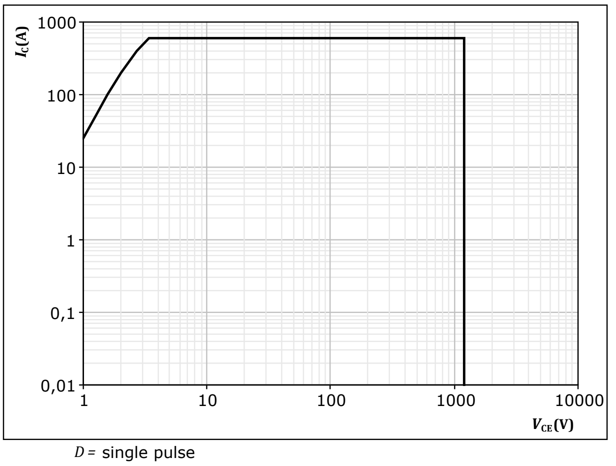
R (K/W)	τ (s)
3,72E-02	4,28E+00
7,68E-02	6,09E-01
1,42E-01	7,68E-02
6,11E-02	1,66E-02
1,38E-02	8,44E-04

Inner Boost Switch Characteristics

figure 5. **IGBT**

Safe operating area

I_C = f(V_{CE})

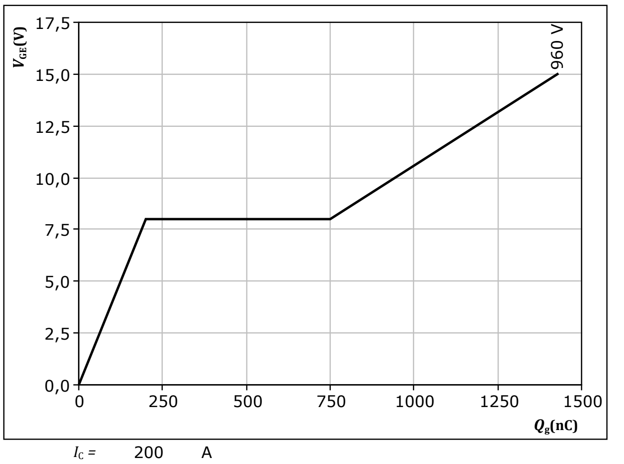


D = single pulse
T_s = 80 °C
V_{GE} = 15 V
T_j = T_{jmax}

figure 6. **IGBT**

Gate voltage vs gate charge

V_{GE} = f(Q_g)



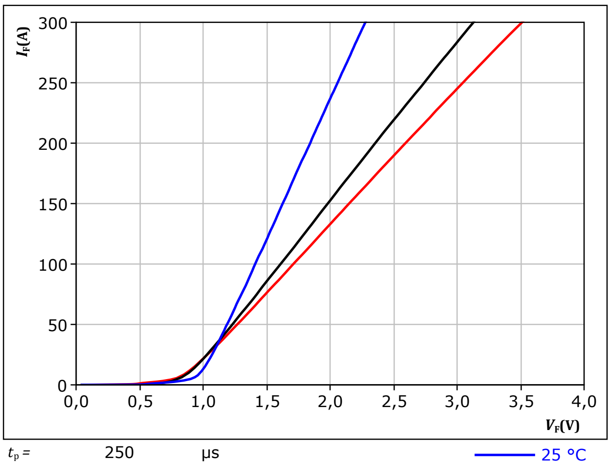
I_C = 200 A
T_j = 25 °C

Inner Boost Diode Characteristics

figure 7. FWD

Typical forward characteristics

I_F = f(V_F)



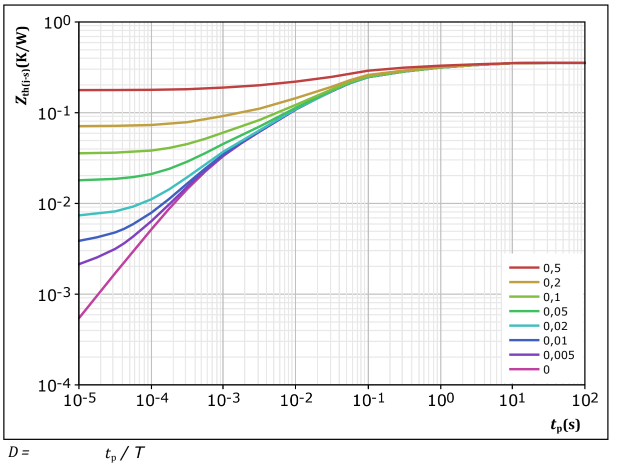
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 8. FWD

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 0,355 K/W

FWD thermal model values

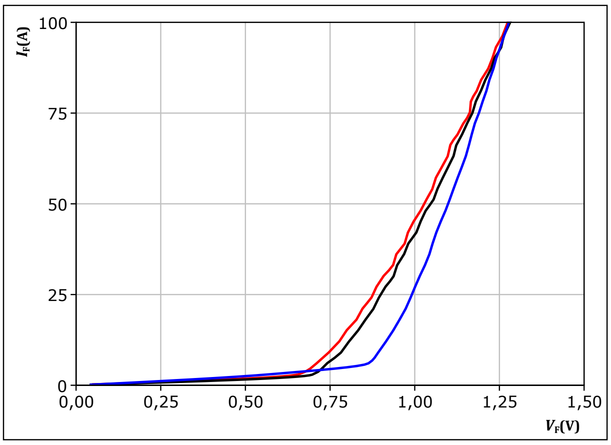
R (K/W)	τ (s)
4,15E-02	3,95E+00
6,08E-02	4,86E-01
1,69E-01	4,49E-02
5,78E-02	5,72E-03
2,55E-02	6,28E-04

Inner Boost Sw. Protection Diode Characteristics

figure 9. **Rectifier**

Typical forward characteristics

I_F = f(V_F)



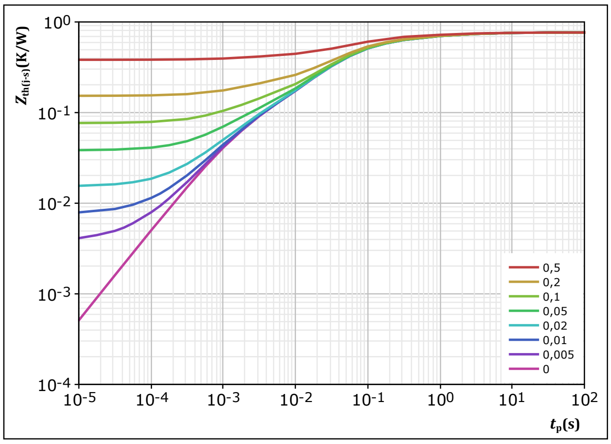
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 10. **Rectifier**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 0,765 K/W

Rectifier thermal model values

R (K/W)	τ (s)
4,68E-02	5,24E+00
1,43E-01	5,88E-01
3,57E-01	7,04E-02
1,61E-01	1,86E-02
5,74E-02	1,54E-03

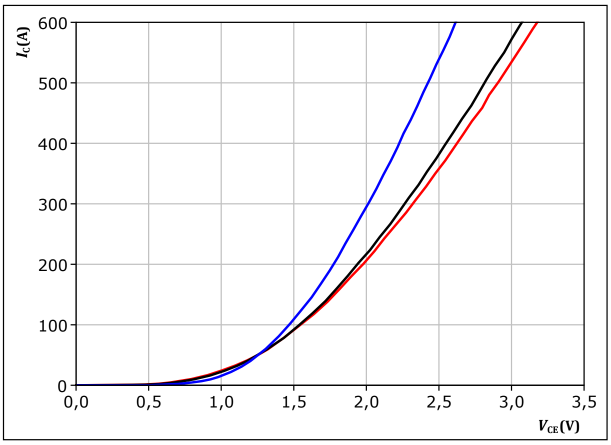
30-PQ12B2A200H703-PK89L07T
datasheet

Outer Boost Switch Characteristics

figure 11. **IGBT**

Typical output characteristics

I_C = f(V_{CE})

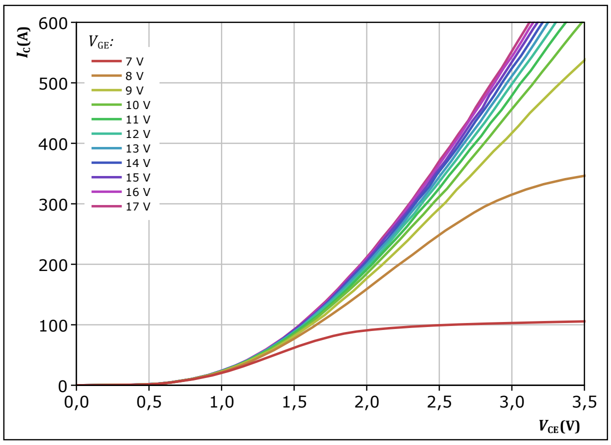


t_p =	250	µs	25 °C
V_{GE} =	15	V	T_j: 125 °C
			150 °C

figure 12. **IGBT**

Typical output characteristics

I_C = f(V_{CE})



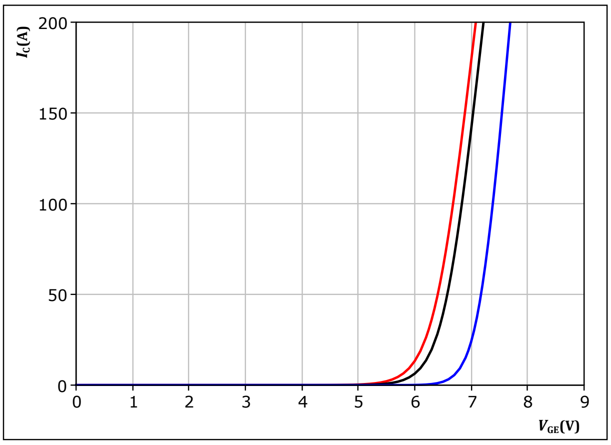
t_p =	250	µs
T_j =	150	°C

V_{GE} from 7 V to 17 V in steps of 1 V

figure 13. **IGBT**

Typical transfer characteristics

I_C = f(V_{GE})

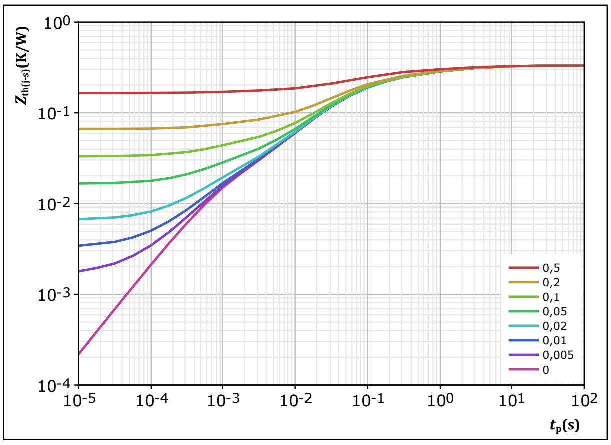


t_p =	250	µs	25 °C
V_{CE} =	48	V	T_j: 125 °C
			150 °C

figure 14. **IGBT**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D =	t_p / T	
$R_{th(j-s)}$ =	0,331	K/W

IGBT thermal model values

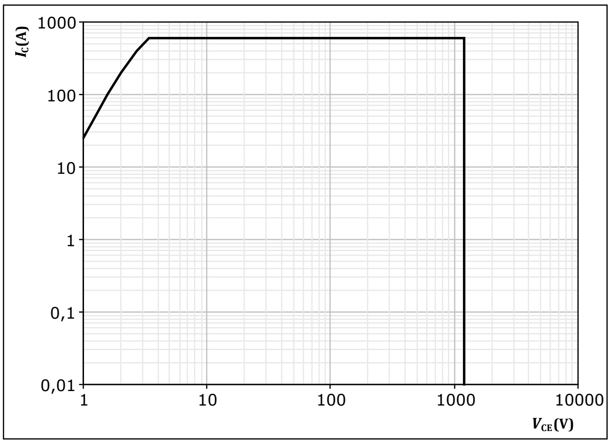
R (K/W)	τ (s)
3,72E-02	4,28E+00
7,68E-02	6,09E-01
1,42E-01	7,68E-02
6,11E-02	1,66E-02
1,38E-02	8,44E-04

Outer Boost Switch Characteristics

figure 15. **IGBT**

Safe operating area

I_C = f(V_{CE})

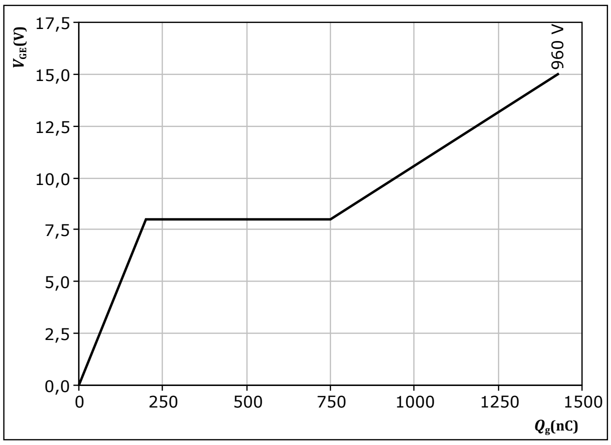


D = single pulse
T_s = 80 °C
V_{GE} = 15 V
T_j = T_{jmax}

figure 16. **IGBT**

Gate voltage vs gate charge

V_{GE} = f(Q_g)



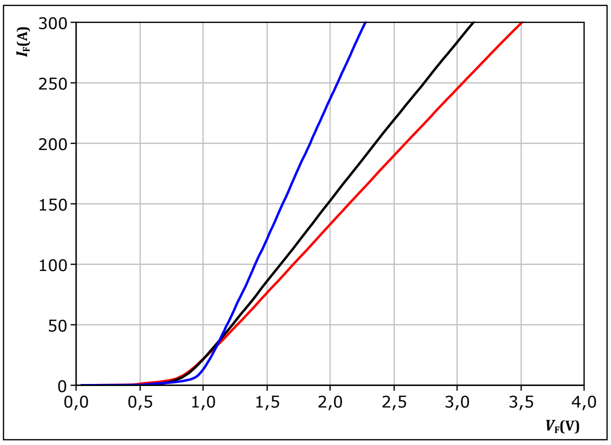
I_C = 200 A
T_j = 25 °C

Outer Boost Diode Characteristics

figure 17. **FWD**

Typical forward characteristics

$I_F = f(V_F)$



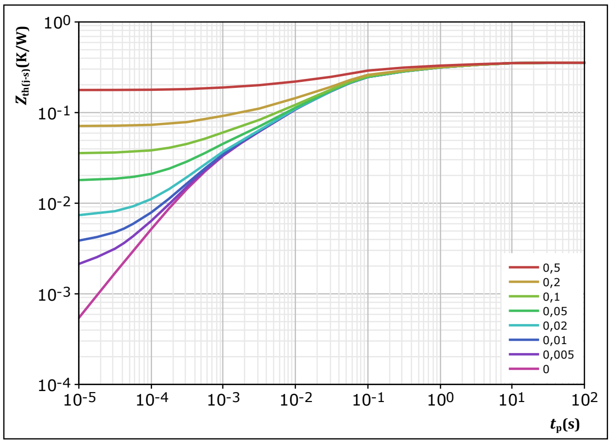
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 18. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 0,355 K/W

FWD thermal model values

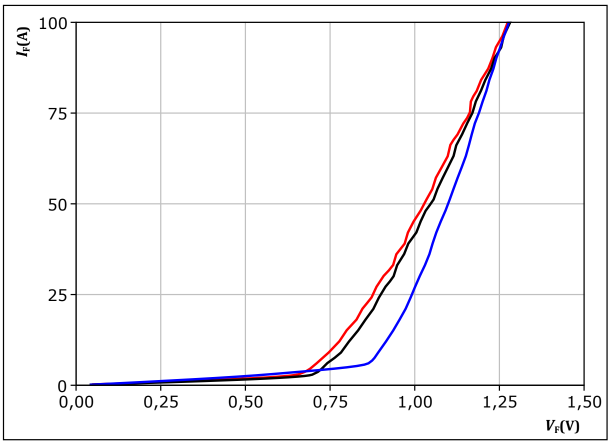
R (K/W)	τ (s)
4,15E-02	3,95E+00
6,08E-02	4,86E-01
1,69E-01	4,49E-02
5,78E-02	5,72E-03
2,55E-02	6,28E-04

Outer Boost Sw. Protection Diode Characteristics

figure 19. **Rectifier**

Typical forward characteristics

I_F = f(V_F)



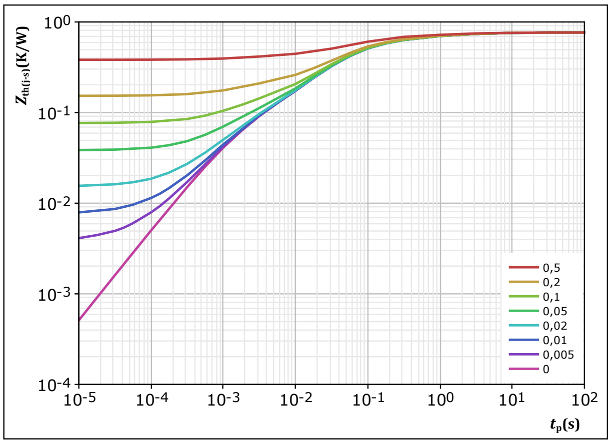
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 20. **Rectifier**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 0,765 K/W

Rectifier thermal model values

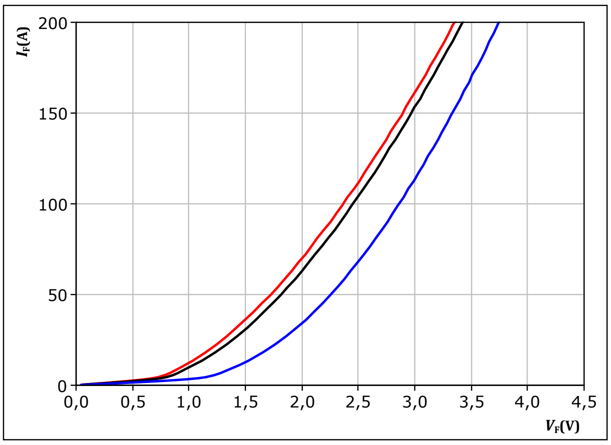
R (K/W)	τ (s)
4,68E-02	5,24E+00
1,43E-01	5,88E-01
3,57E-01	7,04E-02
1,61E-01	1,86E-02
5,74E-02	1,54E-03

Aux Diode Characteristics

figure 21. **FWD**

Typical forward characteristics

I_F = f(V_F)



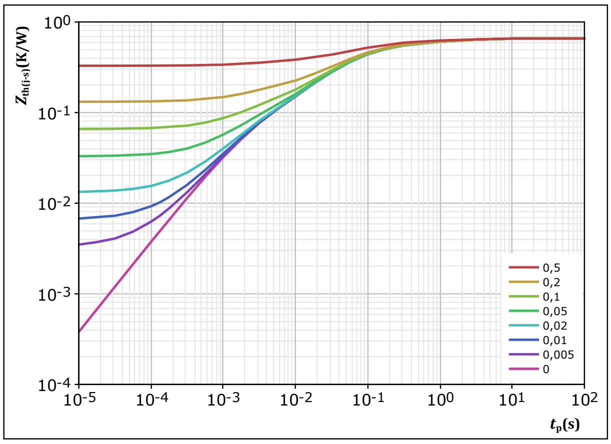
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 22. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 0,657 K/W

FWD thermal model values

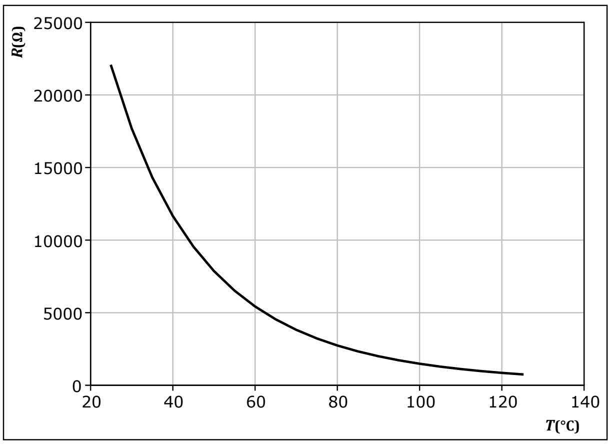
R (K/W)	τ (s)
6,51E-02	2,52E+00
1,04E-01	3,73E-01
3,01E-01	7,08E-02
1,34E-01	1,87E-02
5,30E-02	2,00E-03

Thermistor Characteristics

figure 23.	Thermistor

Typical NTC characteristic as function of temperature

R_T = f(T)

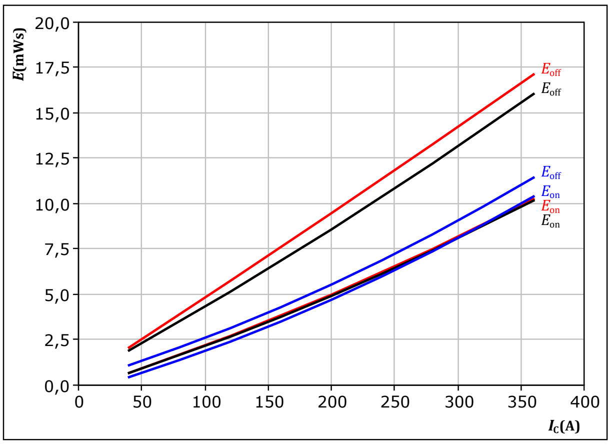


Inner Boost Switching Characteristics

figure 24. **IGBT**

Typical switching energy losses as a function of collector current

E = f(I_C)



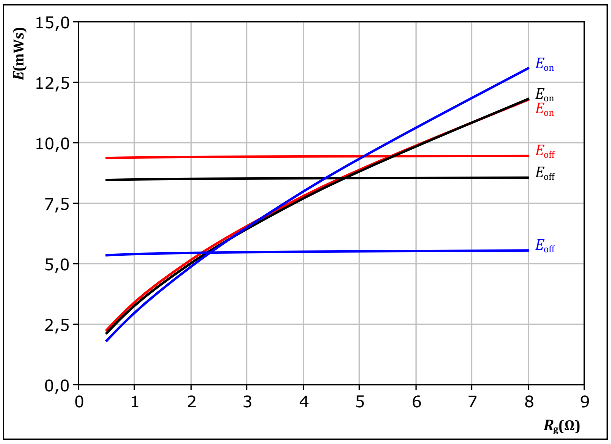
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	2	Ω		150 °C
R_{goff} =	2	Ω		

figure 25. **IGBT**

Typical switching energy losses as a function of IGBT turn on gate resistor

E = f(R_g)



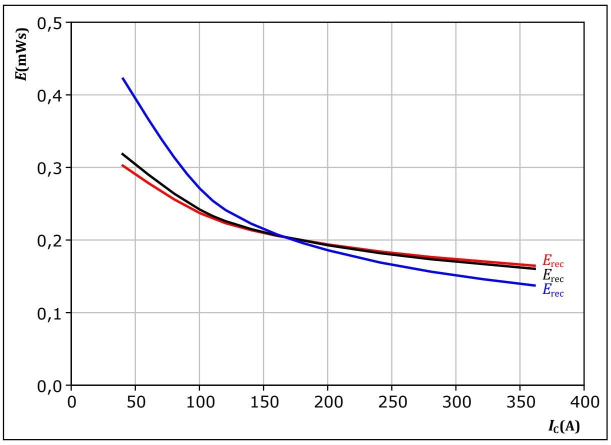
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	200	A		150 °C

figure 26. **FWD**

Typical reverse recovered energy loss as a function of collector current

E_{rec} = f(I_C)



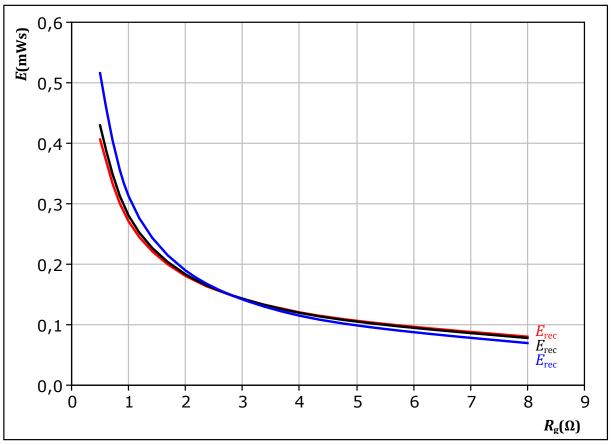
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	2	Ω		150 °C

figure 27. **FWD**

Typical reverse recovered energy loss as a function of IGBT turn on gate resistor

E_{rec} = f(R_g)



With an inductive load at

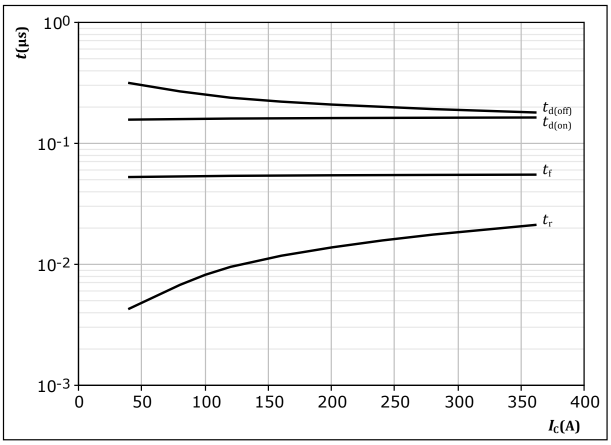
V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	200	A		150 °C

Inner Boost Switching Characteristics

figure 28. **IGBT**

Typical switching times as a function of collector current

t = f(I_C)



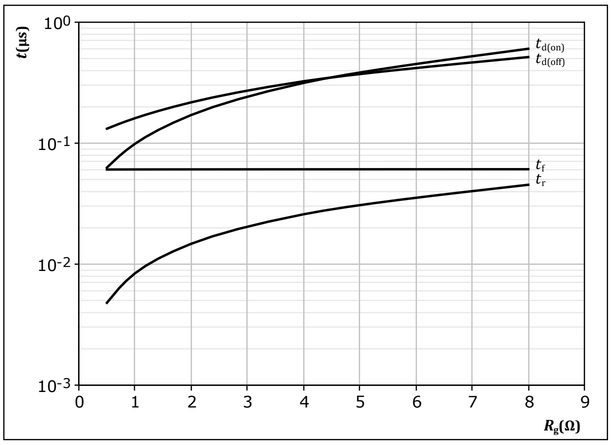
With an inductive load at

T_j =	150	°C
V_{CE} =	700	V
V_{GE} =	±15	V
R_{gon} =	2	Ω
R_{goff} =	2	Ω

figure 29. **IGBT**

Typical switching times as a function of IGBT turn on gate resistor

t = f(R_g)



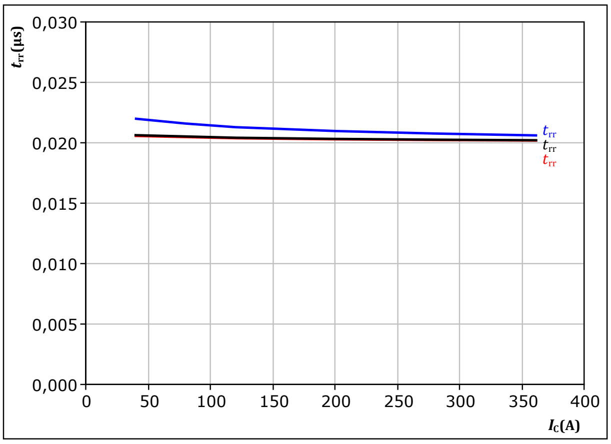
With an inductive load at

T_j =	150	°C
V_{CE} =	700	V
V_{GE} =	±15	V
I_C =	200	A

figure 30. **FWD**

Typical reverse recovery time as a function of collector current

t_{rr} = f(I_C)



With an inductive load at

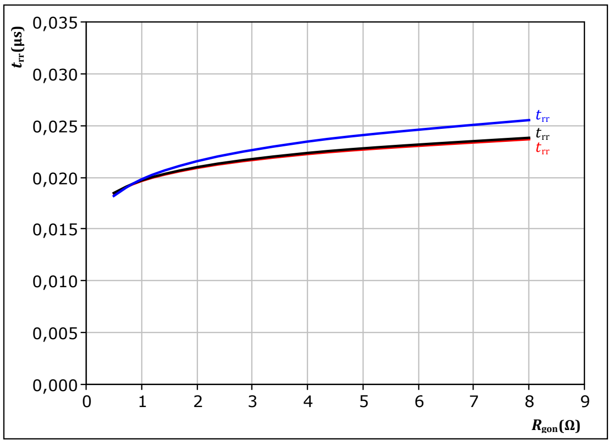
V_{CE} =	700	V
V_{GE} =	±15	V
R_{gon} =	2	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 31. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

t_{rr} = f(R_{gon})



With an inductive load at

V_{CE} =	700	V
V_{GE} =	±15	V
I_C =	200	A

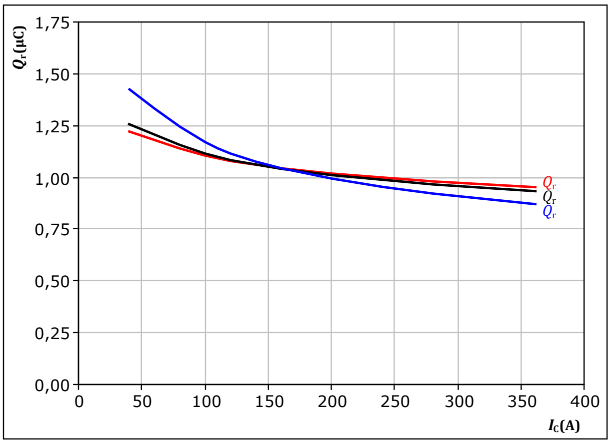
T_j: 25 °C, 125 °C, 150 °C

Inner Boost Switching Characteristics

figure 32. FWD

Typical recovered charge as a function of collector current

Q_r = f(I_C)



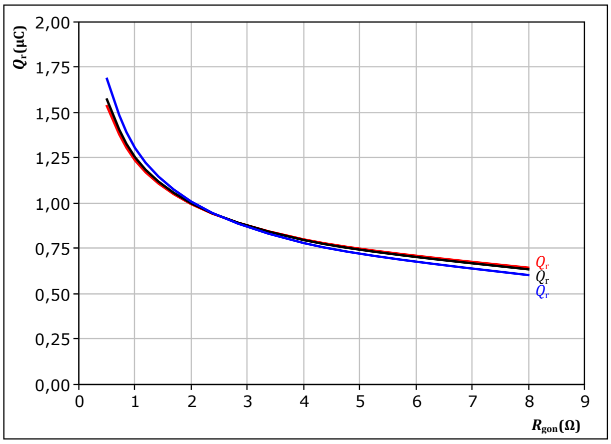
With an inductive load at

V_{CE} =	700	V	T_j: 25 °C / 125 °C / 150 °C
V_{GE} =	±15	V	
R_{gon} =	2	Ω	

figure 33. FWD

Typical recovered charge as a function of IGBT turn on gate resistor

Q_r = f(R_{gon})



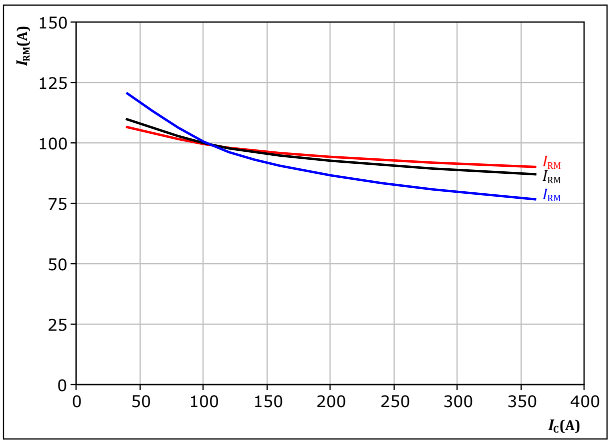
With an inductive load at

V_{CE} =	700	V	T_j: 25 °C / 125 °C / 150 °C
V_{GE} =	±15	V	
I_C =	200	A	

figure 34. FWD

Typical peak reverse recovery current as a function of collector current

I_{RM} = f(I_C)



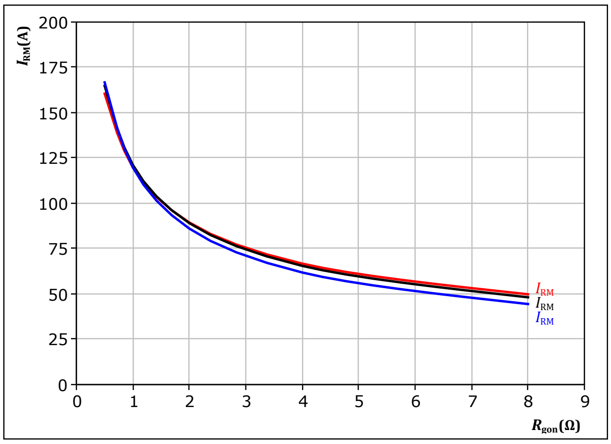
With an inductive load at

V_{CE} =	700	V	T_j: 25 °C / 125 °C / 150 °C
V_{GE} =	±15	V	
R_{gon} =	2	Ω	

figure 35. FWD

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

I_{RM} = f(R_{gon})



With an inductive load at

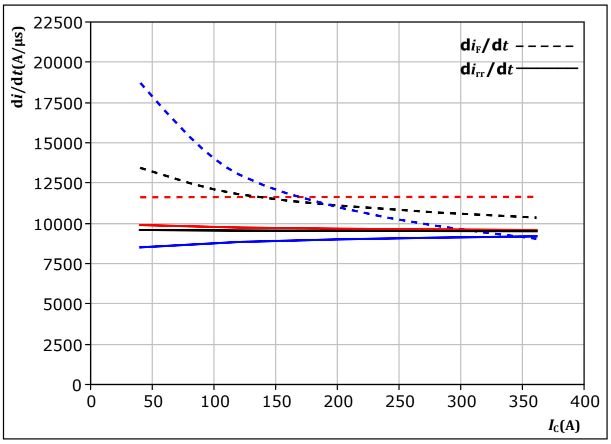
V_{CE} =	700	V	T_j: 25 °C / 125 °C / 150 °C
V_{GE} =	±15	V	
I_C =	200	A	

Inner Boost Switching Characteristics

figure 36. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

di_F/dt, di_{rr}/dt = f(I_C)



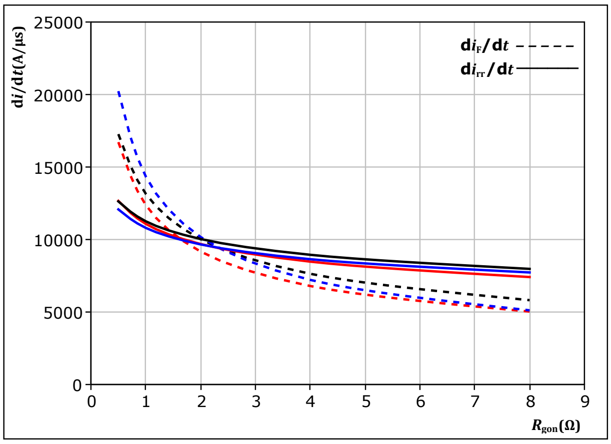
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	2	Ω		150 °C

figure 37. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})



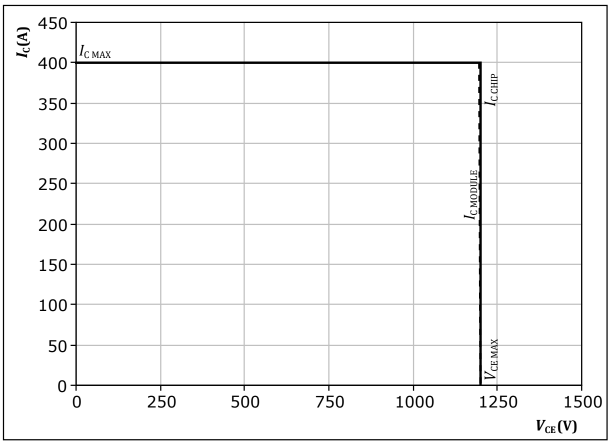
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	200	A		150 °C

figure 38. **IGBT**

Reverse bias safe operating area

I_C = f(V_{CE})



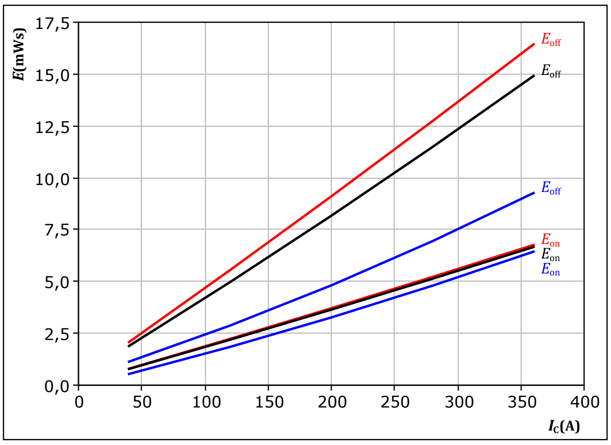
At	T_j =	150	°C
	R_{gon} =	2	Ω
	R_{goff} =	2	Ω

Outer Boost Switching Characteristics

figure 39. **IGBT**

Typical switching energy losses as a function of collector current

$E = f(I_C)$



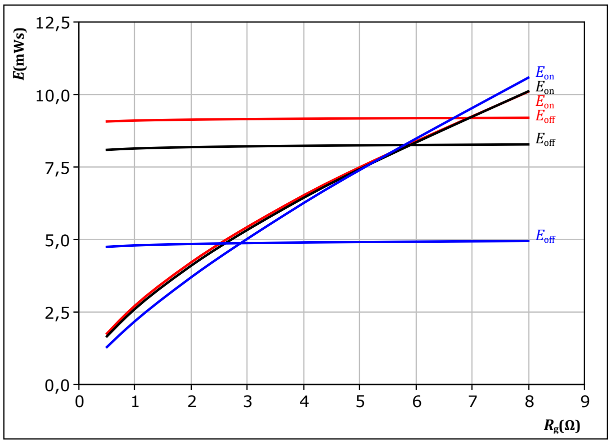
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	2	Ω		150 °C
R_{goff} =	2	Ω		

figure 40. **IGBT**

Typical switching energy losses as a function of IGBT turn on gate resistor

$E = f(R_g)$



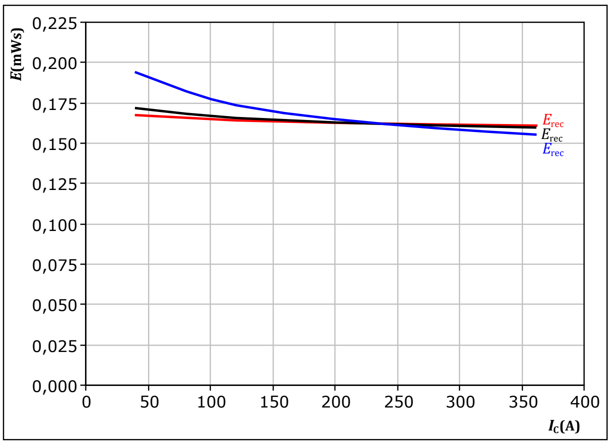
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	200	A		150 °C

figure 41. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_C)$



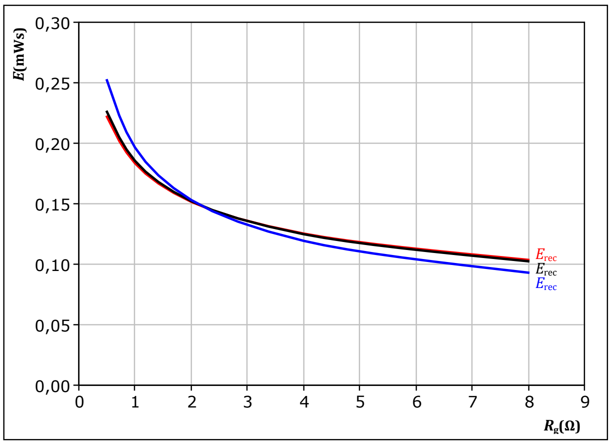
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	2	Ω		150 °C

figure 42. **FWD**

Typical reverse recovered energy loss as a function of IGBT turn on gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

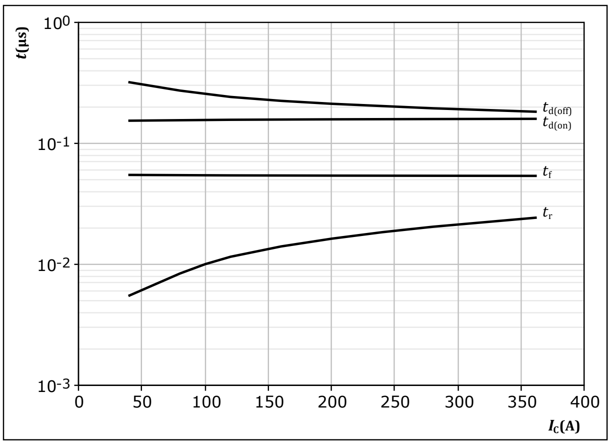
V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	200	A		150 °C

Outer Boost Switching Characteristics

figure 43. **IGBT**

Typical switching times as a function of collector current

$t = f(I_C)$



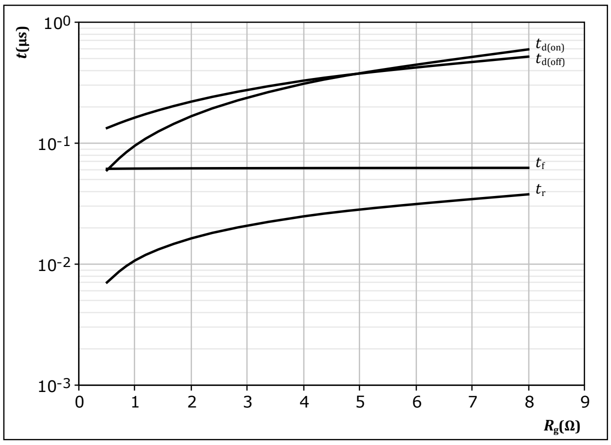
With an inductive load at

T_j =	150	°C
V_{CE} =	700	V
V_{GE} =	±15	V
R_{gon} =	2	Ω
R_{goff} =	2	Ω

figure 44. **IGBT**

Typical switching times as a function of IGBT turn on gate resistor

$t = f(R_g)$



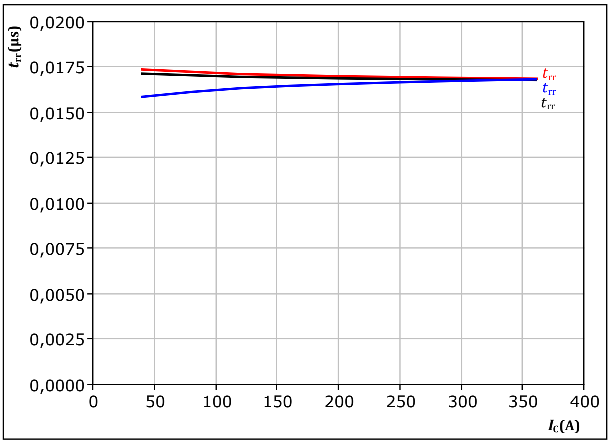
With an inductive load at

T_j =	150	°C
V_{CE} =	700	V
V_{GE} =	±15	V
I_C =	200	A

figure 45. **FWD**

Typical reverse recovery time as a function of collector current

$t_{rr} = f(I_C)$



With an inductive load at

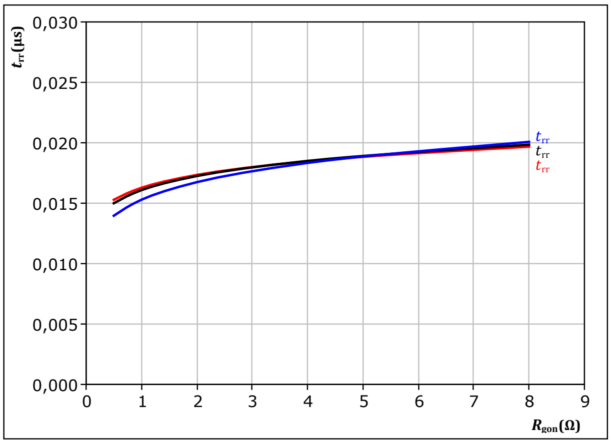
V_{CE} =	700	V
V_{GE} =	±15	V
R_{gon} =	2	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 46. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

$t_{rr} = f(R_{gon})$



With an inductive load at

V_{CE} =	700	V
V_{GE} =	±15	V
I_C =	200	A

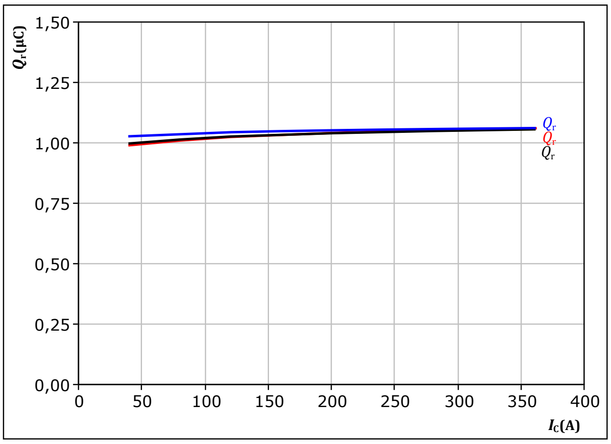
T_j: 25 °C, 125 °C, 150 °C

Outer Boost Switching Characteristics

figure 47. **FWD**

Typical recovered charge as a function of collector current

Q_r = f(I_C)



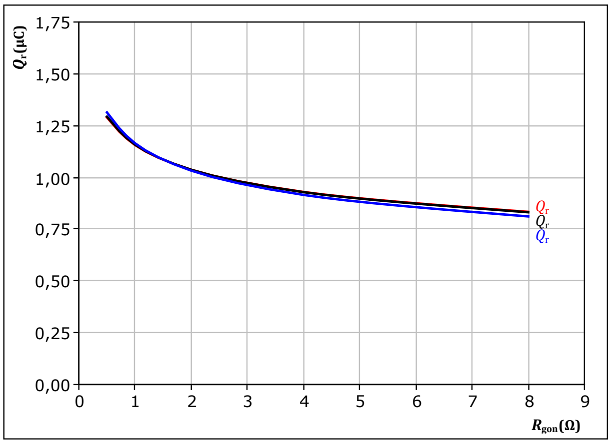
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	2	Ω		150 °C

figure 48. **FWD**

Typical recovered charge as a function of IGBT turn on gate resistor

Q_r = f(R_{gon})



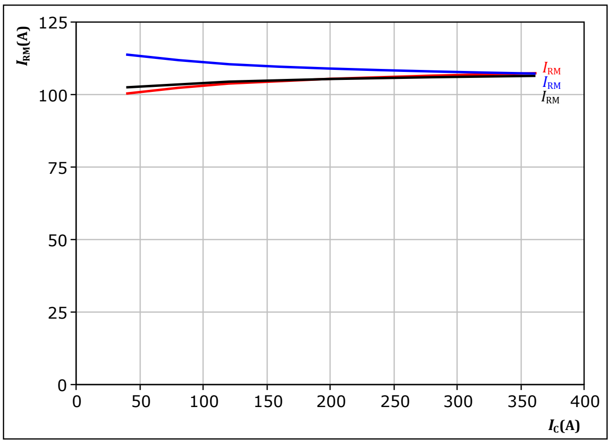
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	200	A		150 °C

figure 49. **FWD**

Typical peak reverse recovery current as a function of collector current

I_{RM} = f(I_C)



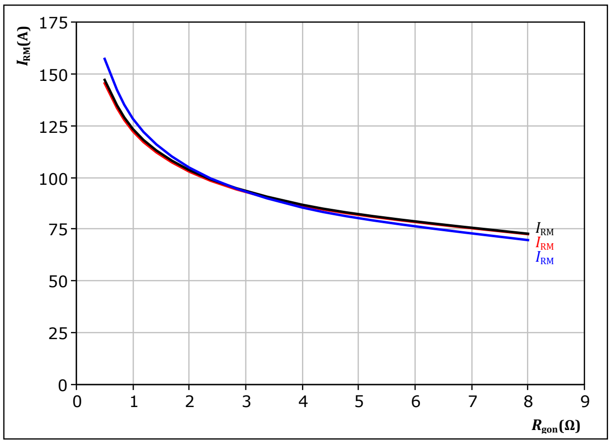
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	2	Ω		150 °C

figure 50. **FWD**

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

I_{RM} = f(R_{gon})



With an inductive load at

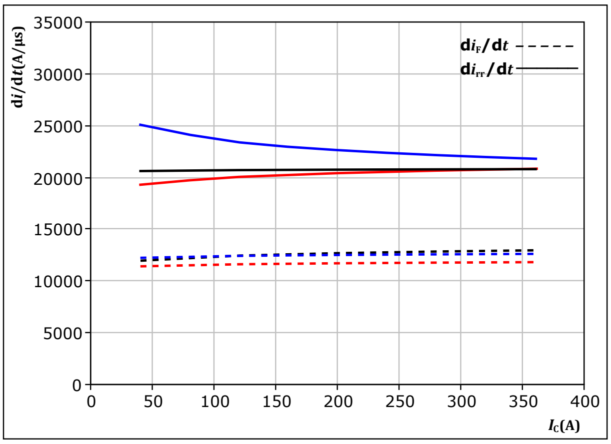
V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	200	A		150 °C

Outer Boost Switching Characteristics

figure 51. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

di_F/dt, di_{rr}/dt = f(I_C)



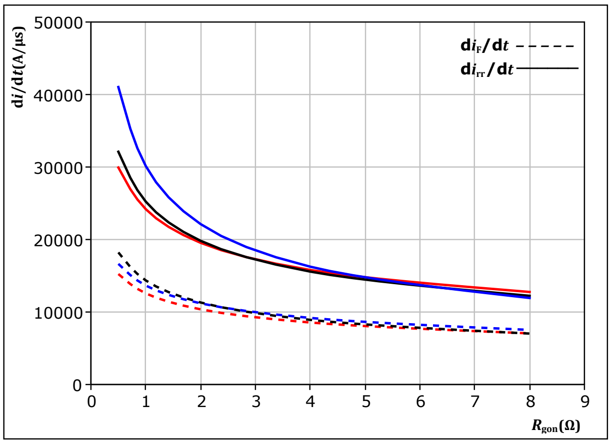
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	2	Ω		150 °C

figure 52. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})



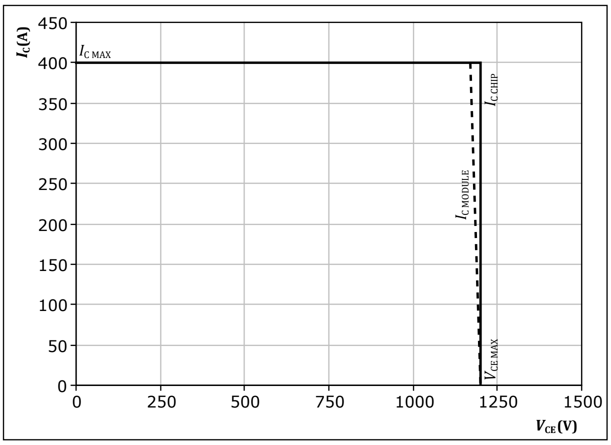
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	200	A		150 °C

figure 53. **IGBT**

Reverse bias safe operating area

I_C = f(V_{CE})



At	T_j =	150	°C
	R_{gon} =	2	Ω
	R_{goff} =	2	Ω

Switching Definitions

figure 54. **IGBT**

Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{tEoff} = integrating time for E_{off})

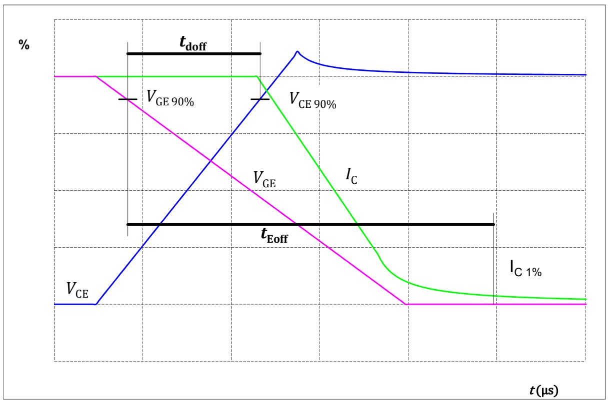


figure 55. **IGBT**

Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} = integrating time for E_{on})

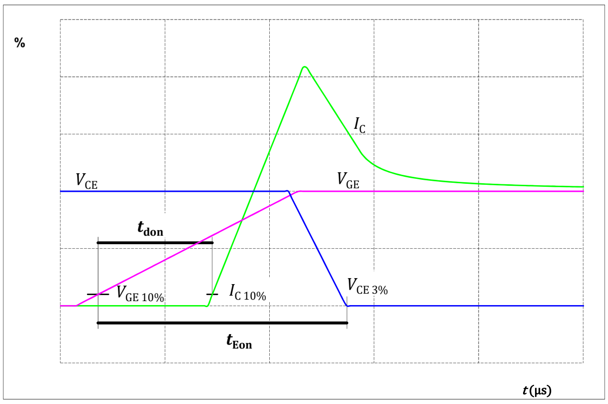


figure 56. **IGBT**

Turn-off Switching Waveforms & definition of t_f

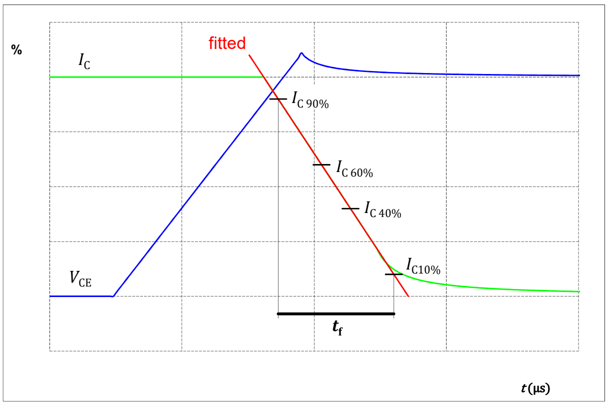
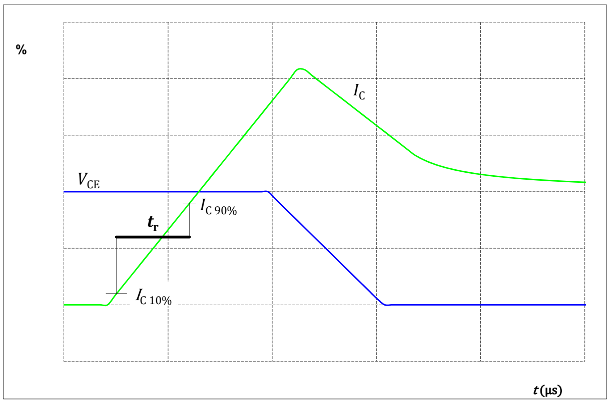


figure 57. **IGBT**

Turn-on Switching Waveforms & definition of t_r



Switching Definitions

figure 58. FWD

Turn-off Switching Waveforms & definition of t_{rr}

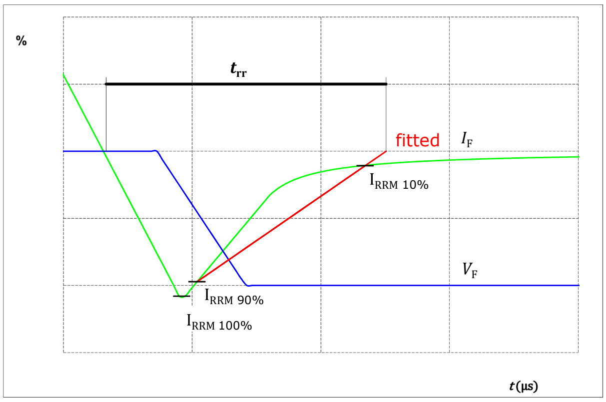
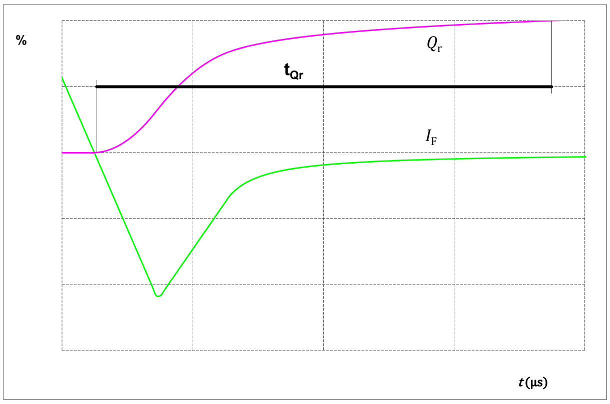


figure 59. FWD

Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)



Ordering Code

Version	Ordering Code
Without thermal paste	30-PQ12B2A200H703-PK89L07T
With thermal paste (3,4 W/mK, PSX-P7)	30-PQ12B2A200H703-PK89L07T-/3/

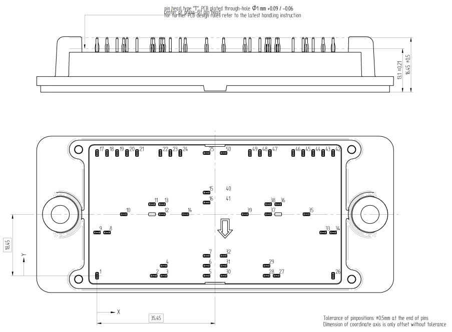
Marking

	Name		Date code	UL & VIN	Lot	Serial
Text	NN-NNNNNNNNNNNNNN-TTTTTTVV		WWYY	UL VIN	LLLLL	SSSS
Datamatrix	**Type&Ver**	**Lot number**	**Serial**	**Date code**		
	TTTTTTTVV	LLLLL	SSSS	WWYY		

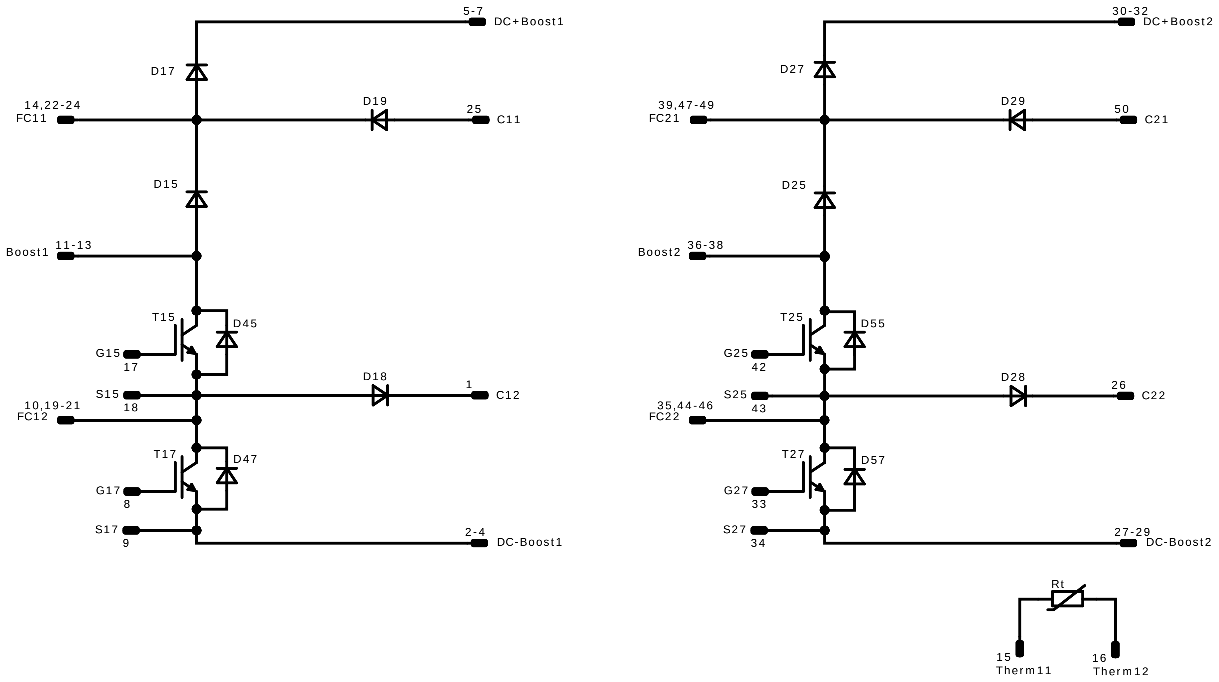
Outline

Pin table [mm]

Pin	X	Y	Function	26	70,9	0	C22
1	0	0	C12	27	53,9	0	DC-Boost2
2	17	0	DC-Boost1	28	50,9	0	DC-Boost2
3	20	0	DC-Boost1	29	50,9	3	DC-Boost2
4	20	3	DC-Boost1	30	38	0	DC+Boost2
5	32,9	0	DC+Boost1	31	38	3	DC+Boost2
6	32,9	3	DC+Boost1	32	38	6	DC+Boost2
7	32,9	6	DC+Boost1	33	67,9	13	G27
8	3	13	G17	34	70,9	13	S27
9	0	13	S17	35	62,9	18,5	FC22
10	8	18,5	FC12	36	54,4	21,5	Boost2
11	16,5	21,5	Boost1	37	51,4	18,5	Boost2
12	19,5	18,5	Boost1	38	51,4	21,5	Boost2
13	19,5	21,5	Boost1	39	44,4	18,5	FC21
14	26,5	18,5	FC11	40	not assembled		
15	32,9	25	Therm11	41	not assembled		
16	32,9	22	Therm12	42	70,9	36,9	G25
17	0	36,9	G15	43	67,9	36,9	S25
18	3	36,9	S15	44	64,9	36,9	FC22
19	6	36,9	FC12	45	61,9	36,9	FC22
20	9	36,9	FC12	46	58,9	36,9	FC22
21	12	36,9	FC12	47	51,9	36,9	FC21
22	19	36,9	FC11	48	48,9	36,9	FC21
23	22	36,9	FC11	49	45,9	36,9	FC21
24	25	36,9	FC11	50	38	36,9	C21
25	32,9	36,9	C11				



Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T15, T25	IGBT	1200 V	200 A	Inner Boost Switch	
D15, D25	FWD	1200 V	100 A	Inner Boost Diode	
D45, D55	Rectifier	1600 V	40 A	Inner Boost Sw. Protection Diode	
T17, T27	IGBT	1200 V	200 A	Outer Boost Switch	
D17, D27	FWD	1200 V	100 A	Outer Boost Diode	
D47, D57	Rectifier	1600 V	40 A	Outer Boost Sw. Protection Diode	
D18, D28, D19, D29	FWD	1200 V	75 A	Aux Diode	
Rt	Thermistor			Thermistor	

Packaging instruction				
Standard packaging quantity (SPQ) 36	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* 2 packages see vincotech.com website.

Package data
Package data for *flow* 2 packages see vincotech.com website.

Vincotech thermistor reference
See Vincotech thermistor reference table at vincotech.com website.

UL recognition and file number
This device is UL 1557 recognized under E192116 up to a junction temperature under switching condition $T_{j,op}$=175°C and up to 4000VAC/1min isolation voltage. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
30-PQ12B2A200H703-PK89L07T-D1-14	30 Mar. 2025	Initial Release	